TLV1117LV 1-A, Positive Fixed-Voltage, Low-Dropout Regulator

1 Features

- Typical accuracy: 1.5%
- Low I_Q: 100 µA (maximum)
  - 500 times lower than standard 1117 devices
- V_{IN}: 2 V to 5.5 V
  - Absolute maximum V_{IN}: 6 V
- Stable With 0-mA output current
- Low dropout: 455 mV at 1 A for V_{OUT} = 3.3 V
- High PSRR: 65 dB at 1 kHz
- Minimum specified current limit: 1.1 A
- Stable with cost-effective ceramic capacitors:
  - With 0-Ω ESR
- Temperature range: –40°C to +125°C
- Thermal shutdown and overcurrent protection
- For drop-in replacement with upgraded functionality, see the TLV761
- Available in a SOT-223 package
  - See the *Mechanical, Packaging, and Orderable Information* section at the end of this document for a complete list of available voltage options.

2 Applications

- Set-top boxes
- TVs and monitors
- PC peripherals, notebooks, motherboards
- Modems and other communication products
- Switching power supply post-regulation

3 Description

The TLV1117LV low-dropout (LDO) linear regulator is a low input voltage version of the popular TLV1117 voltage regulator.

The TLV1117LV is an extremely low-power device that consumes 500 times lower quiescent current than traditional 1117 voltage regulators, making the device designed for applications that mandate very low standby current. The TLV1117LV LDO is also stable with 0 mA of load current; there is no minimum load requirement, making the device a good choice for applications where the regulator must power very small loads during standby in addition to large currents on the order of 1 A during normal operation. The TLV1117LV offers excellent line and load transient performance, resulting in very small magnitude undershoots and overshoots of output voltage when the load current requirement changes from less than 1 mA to more than 500 mA.

A precision band-gap and error amplifier provides 1.5% accuracy. A very high power-supply rejection ratio (PSRR) enables use of the device for post-regulation after a switching regulator. Other valuable features include low output noise and low-dropout voltage.

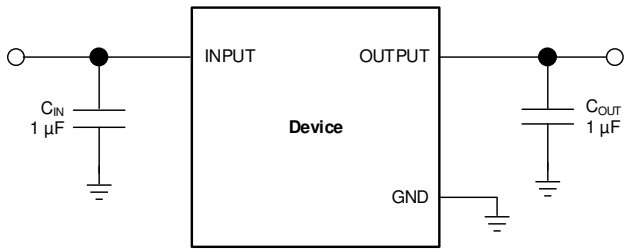
The device is internally compensated to be stable with 0-Ω equivalent series resistance (ESR) capacitors. These key advantages enable the use of cost-effective, small-size ceramic capacitors. Cost-effective capacitors that have higher bias voltages and temperature derating can also be used if desired.

The TLV1117LV is available in a SOT-223 package.

Package Information

PART NUMBER	PACKAGE(1)	BODY SIZE (NOM)
TLV1117LV	DCY (SOT-223, 4)	6.50 mm × 3.50 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Typical Application Circuit

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (January 2015) to Revision C (January 2023)	Page
• Added drop-in replacement bullet to *Features* section	1

Changes from Revision A (September 2011) to Revision B (January 2015)	Page
• Added *ESD Ratings* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section	1
• Replaced front-page figure	1
• Deleted *Dissipation Ratings* table	4

5 Pin Configuration and Functions

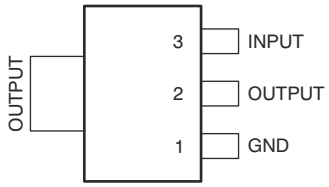


Figure 5-1. DCY Package, 4 Pins (SOT-223) (Top View)

Table 5-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
IN	3	I	Input pin. See the *Input and Output Capacitor Requirements* section for more details.
OUT	2, Tab	O	Regulated output voltage pin. See the *Input and Output Capacitor Requirements* section for more details.
GND	1	—	Ground pin.

6 Specifications

6.1 Absolute Maximum Ratings

at T_J = 25°C (unless otherwise noted); all voltages are with respect to GND[1]

		MIN	MAX	UNIT
Voltage	V_{IN}	–0.3	6	V
	V_{OUT}	–0.3	6	V
Current	I_{OUT}	Internally limited		
Output short-circuit duration		Indefinite		
Continuous total power dissipation	P_{DISS}	See *Thermal Information*		
Temperature	Operating junction, T_J	–55	150	°C
	Storage, T_{stg}	–55	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins[1]	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins[2]	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{IN}	Input voltage	2		5.5	V
V_{OUT}	Output voltage	0		5.5	V
I_{OUT}	Output current	0		1	A

6.4 Thermal Information

THERMAL METRIC[1]		TLV1117LV DCY (SOT-223) 4 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	62.9	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance	47.2	°C/W
$R_{\theta JC(top)}$	Junction-to-board thermal resistance	12	°C/W
ψ_{JT}	Junction-to-top characterization parameter	6.1	°C/W
ψ_{JB}	Junction-to-board characterization parameter	11.9	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application note.

6.5 Electrical Characteristics

at V_{IN} = $V_{OUT(nom)}$ + 1.5 V; I_{OUT} = 10 mA, C_{OUT} = 1.0 µF, and T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V_{IN}	Input voltage				2		5.5	V
V_{OUT}	DC output accuracy	V_{OUT} > 2 V			–1.5%		1.5%	
		1.5 V ≤ V_{OUT} < 2 V			–2%		2%	
		1.2 V ≤ V_{OUT} < 1.5 V			–40		40	mV
$\Delta V_{OUT(\Delta VIN)}$	Line regulation	$V_{OUT(nom)}$ + 0.5 V ≤ V_{IN} ≤ 5.5 V, I_{OUT} = 10 mA				1	5	mV
$\Delta V_{OUT(\Delta IOUT)}$	Load regulation	0 mA ≤ I_{OUT} ≤ 1 A				1	35	mV
V_{DO}	Dropout voltage(1)	V_{IN} = 0.98 × $V_{OUT(nom)}$	V_{OUT} < 3.3 V	I_{OUT} = 200 mA		115		mV
				I_{OUT} = 500 mA		285		
				I_{OUT} = 800 mA		455		
				I_{OUT} = 1 A		570	800	
			V_{OUT} ≥ 3.3 V	I_{OUT} = 200 mA		90		
				I_{OUT} = 500 mA		230		
				I_{OUT} = 800 mA		365		
				I_{OUT} = 1 A		455	700	
I_{CL}	Output current limit	V_{OUT} = 0.9 × $V_{OUT(nom)}$			1.1			A
I_Q	Quiescent current	I_{OUT} = 0 mA				50	100	µA
PSRR	Power-supply rejection ratio	V_{IN} = 3.3 V, V_{OUT} = 1.8 V, I_{OUT} = 500 mA, f = 100 Hz				65		dB
V_n	Output noise voltage	BW = 10 Hz to 100 kHz, V_{IN} = 2.8 V, V_{OUT} = 1.8 V, I_{OUT} = 500 mA				60		μV_{RMS}
t_{STR}	Start-up time(2)	C_{OUT} = 1.0 µF, I_{OUT} = 1 A				100		µs
UVLO	Undervoltage lockout	V_{IN} rising				1.95		V
T_{SD}	Thermal shutdown temperature	Shutdown, temperature increasing				165		°C
		Reset, temperature decreasing				145		
T_J	Operating junction temperature				–40		125	°C

(1) V_{DO} is measured for devices with $V_{OUT(nom)}$ = 2.5 V so that V_{IN} = 2.45 V.
(2) Start-up time = time from when V_{IN} asserts to when output is sustained at a value greater than or equal to 0.98 × $V_{OUT(nom)}$.

6.6 Typical Characteristics

at V_{IN} = $V_{OUT(nom)}$ + 1.5 V, I_{OUT} = 10 mA, C_{OUT} = 1.0 µF, and T_A = 25°C (unless otherwise noted)

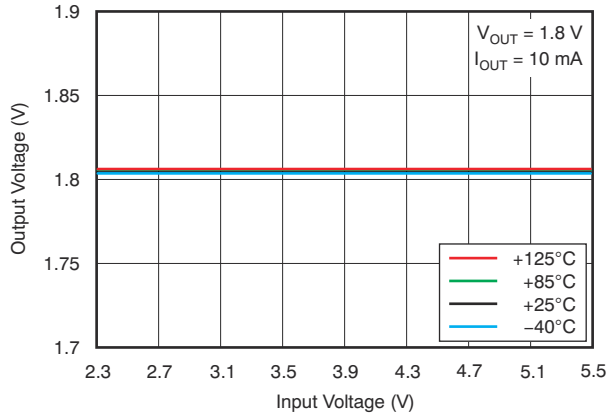


Figure 6-1. Line Regulation

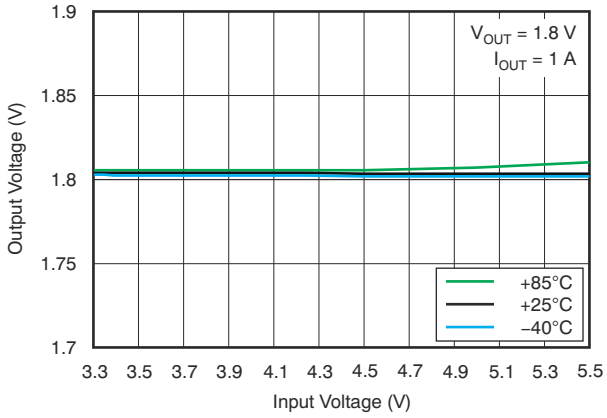


Figure 6-2. Line Regulation

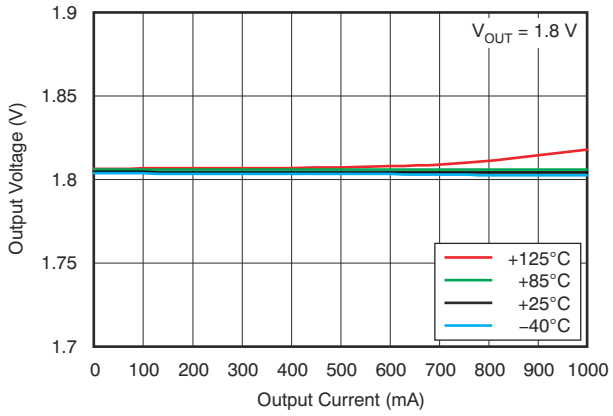


Figure 6-3. Load Regulation

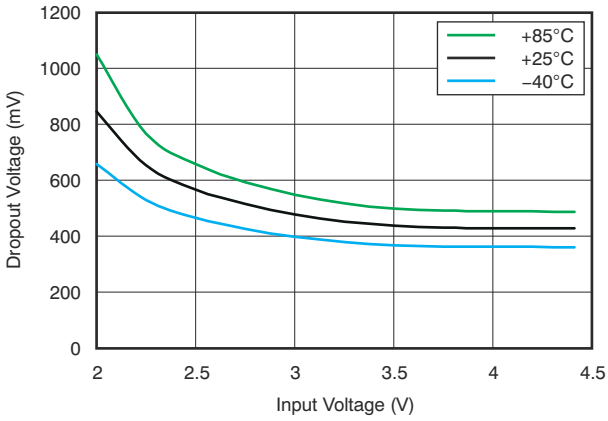


Figure 6-4. Dropout Voltage vs Input Voltage

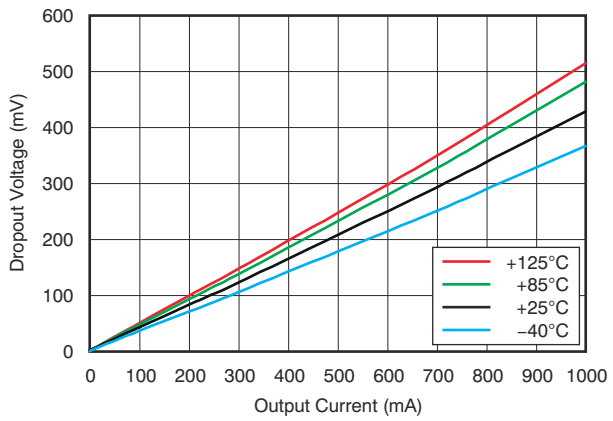


Figure 6-5. Dropout Voltage vs Output Current

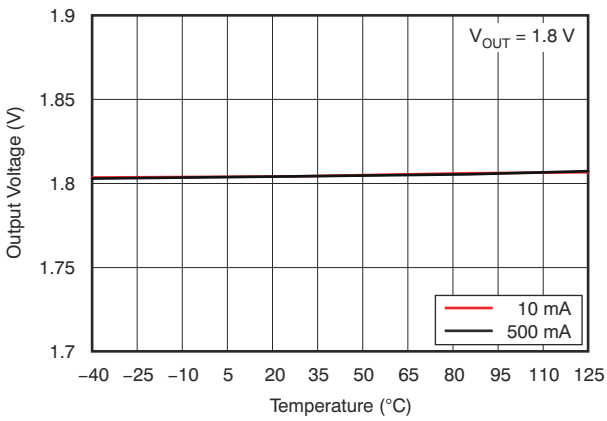


Figure 6-6. Output Voltage vs Temperature

6.6 Typical Characteristics (continued)

at V_{IN} = $V_{OUT(nom)}$ + 1.5 V, I_{OUT} = 10 mA, C_{OUT} = 1.0 µF, and T_A = 25°C (unless otherwise noted)

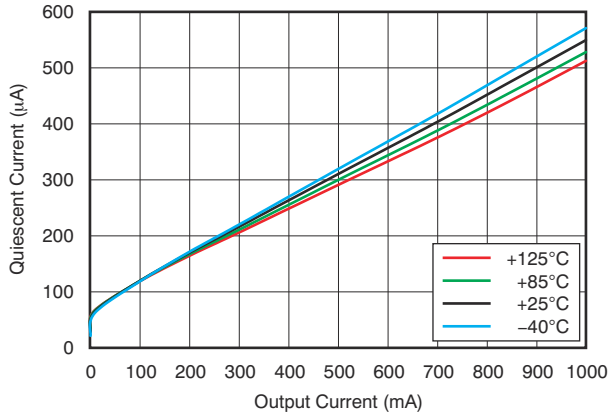


Figure 6-7. Quiescent Current vs Load

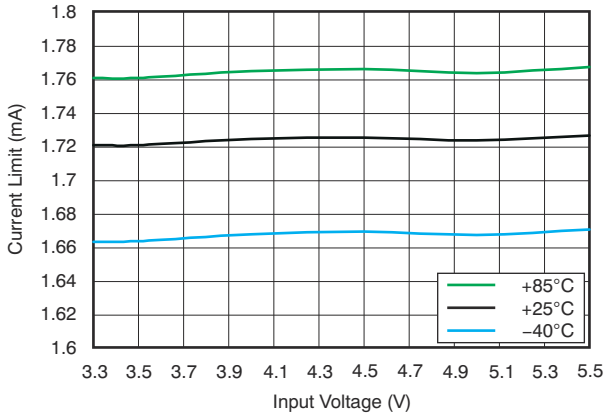


Figure 6-8. Current Limit vs Input Voltage

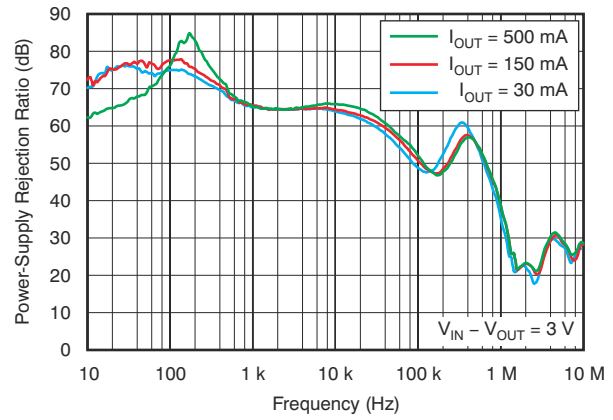


Figure 6-9. Power-Supply Rejection Ratio vs Frequency

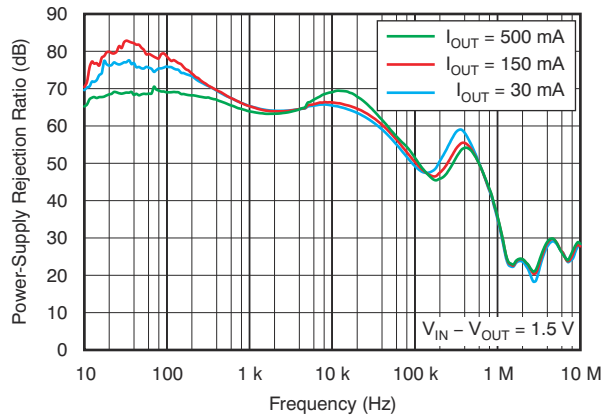


Figure 6-10. Power-Supply Rejection Ratio vs Frequency

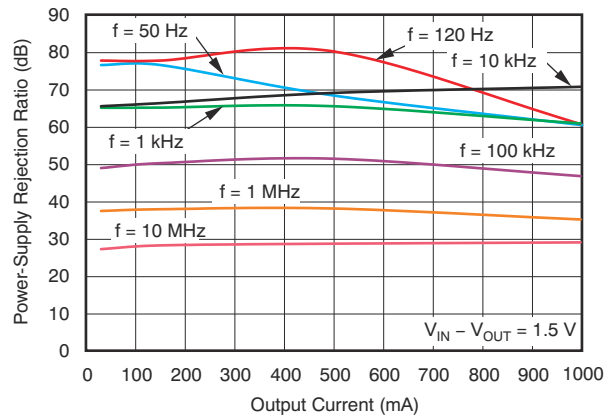


Figure 6-11. Power-Supply Rejection Ratio vs Output Current

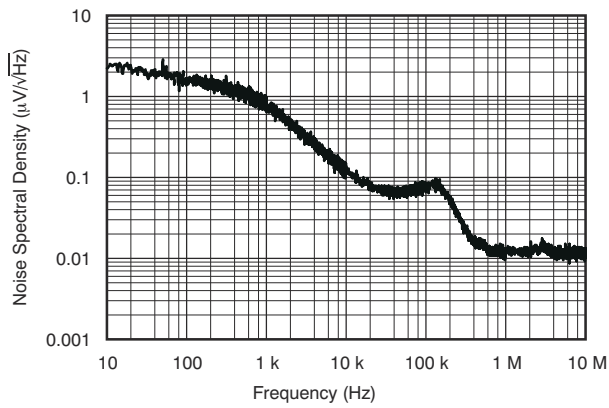
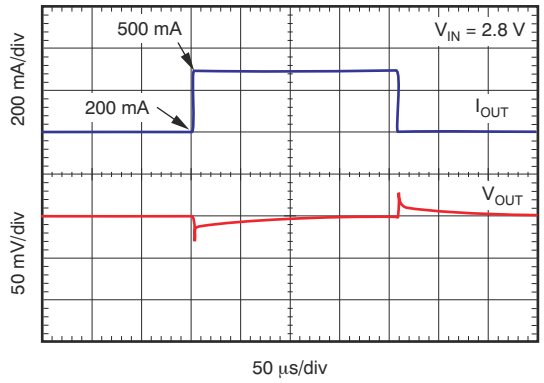


Figure 6-12. Spectral Noise Density vs Frequency

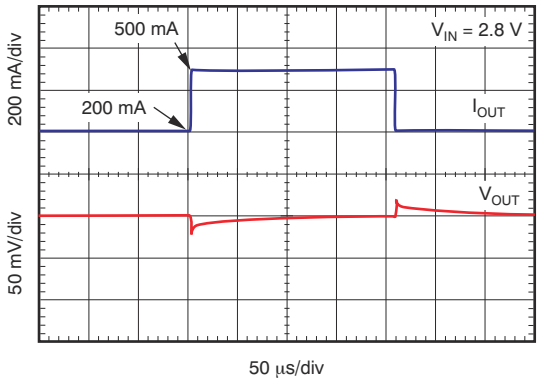
6.6 Typical Characteristics (continued)

at V_{IN} = $V_{OUT(nom)}$ + 1.5 V, I_{OUT} = 10 mA, C_{OUT} = 1.0 µF, and T_A = 25°C (unless otherwise noted)



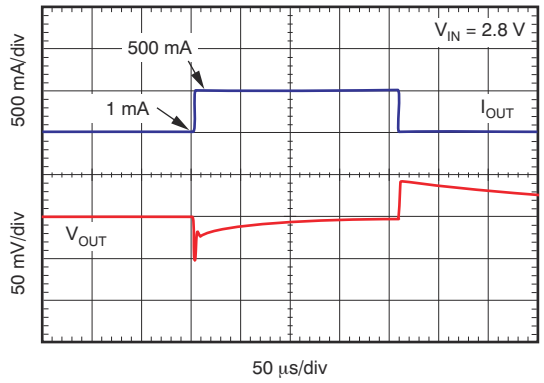
C_{OUT} = 1 µF

Figure 6-13. Load Transient Response 200 mA to 500 mA



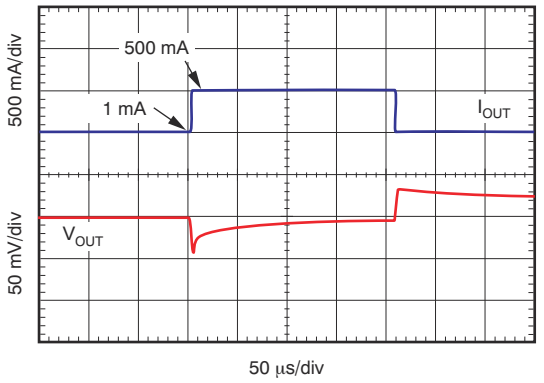
C_{OUT} = 10 µF

Figure 6-14. Load Transient Response 200 mA to 500 mA



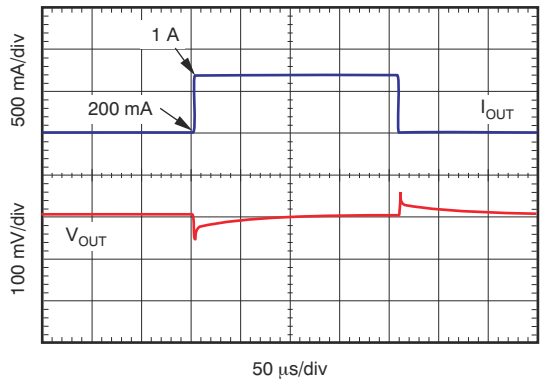
C_{OUT} = 1 µF

Figure 6-15. Load Transient Response 1 mA to 500 mA



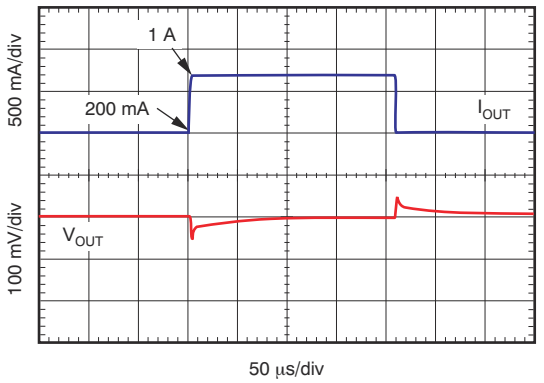
C_{OUT} = 10 µF

Figure 6-16. Load Transient Response 1 mA to 500 mA



C_{OUT} = 1 µF

Figure 6-17. Load Transient Response 200 mA to 1 A

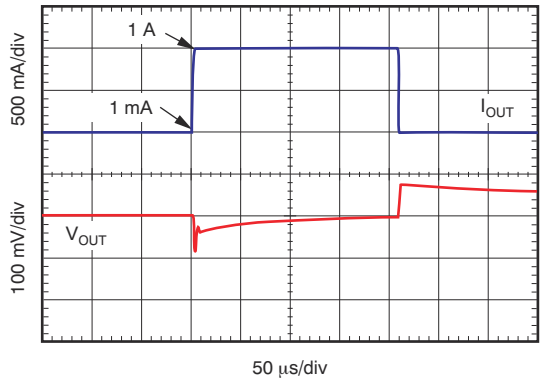


C_{OUT} = 10 µF

Figure 6-18. Load Transient Response 200 mA to 1 A

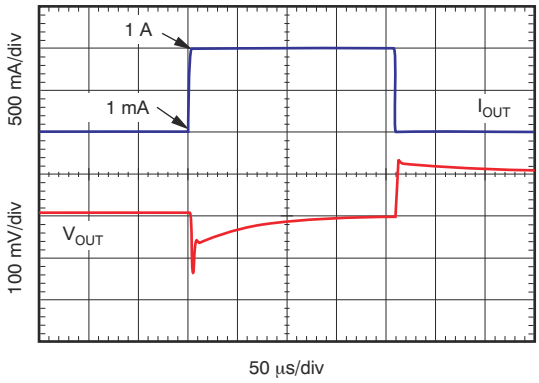
6.6 Typical Characteristics (continued)

at V_{IN} = $V_{OUT(nom)}$ + 1.5 V, I_{OUT} = 10 mA, C_{OUT} = 1.0 µF, and T_A = 25°C (unless otherwise noted)



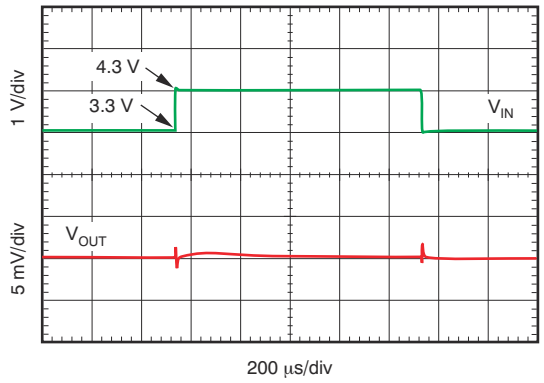
C_{OUT} = 1 µF

Figure 6-19. Load Transient Response 1 mA to 1 A



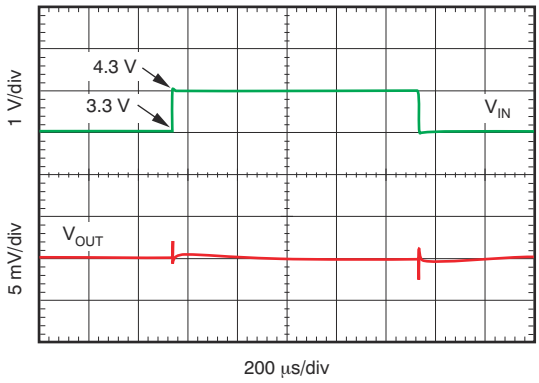
C_{OUT} = 10 µF

Figure 6-20. Load Transient Response 1 mA to 1 A



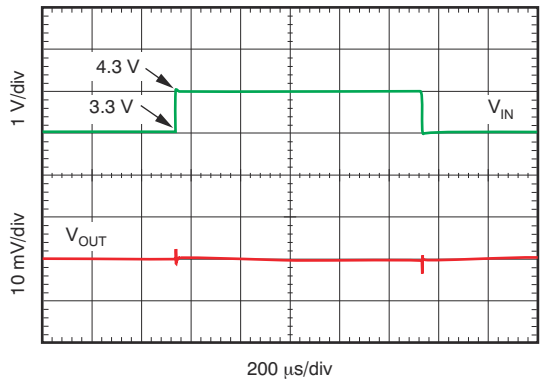
V_{OUT} = 1.8 V, I_{OUT} = 10 mA

Figure 6-21. Line Transient Response



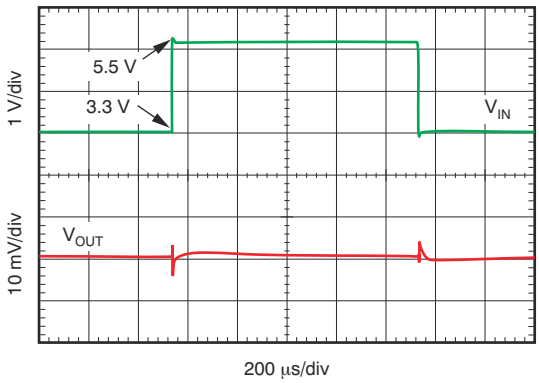
V_{OUT} = 1.8 V, I_{OUT} = 500 mA

Figure 6-22. Line Transient Response



V_{OUT} = 1.8 V, I_{OUT} = 1 A

Figure 6-23. Line Transient Response

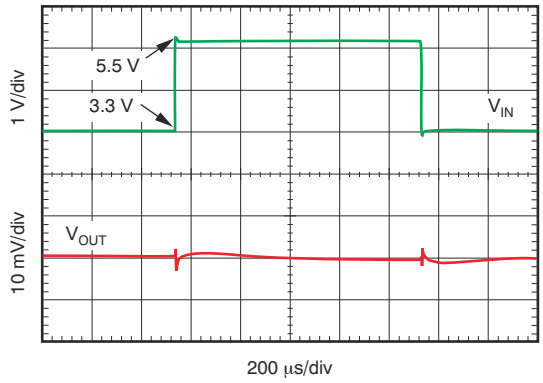


V_{OUT} = 1.8 V, I_{OUT} = 10 mA

Figure 6-24. Line Transient Response

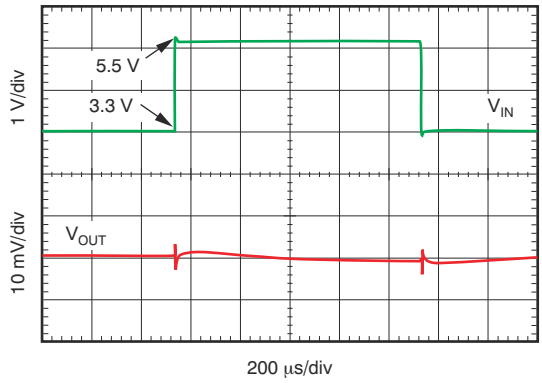
6.6 Typical Characteristics (continued)

at V_{IN} = $V_{OUT(nom)}$ + 1.5 V, I_{OUT} = 10 mA, C_{OUT} = 1.0 µF, and T_A = 25°C (unless otherwise noted)



V_{OUT} = 1.8 V, I_{OUT} = 500 mA

Figure 6-25. Line Transient Response



V_{OUT} = 1.8 V, I_{OUT} = 1 A

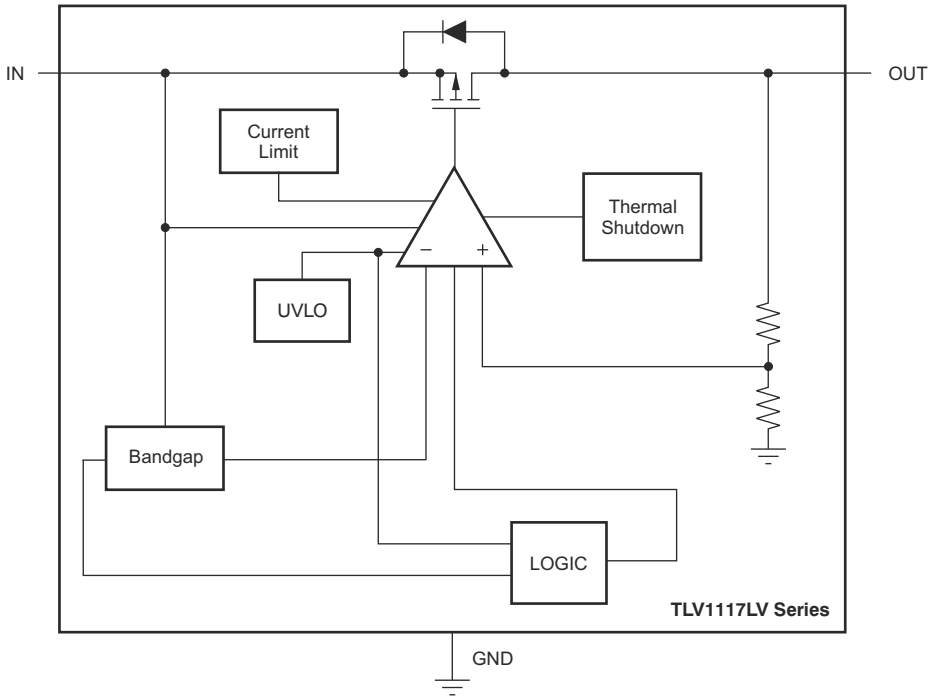
Figure 6-26. Line Transient Response

7 Detailed Description

7.1 Overview

The TLV1117LV is a low quiescent current, high PSRR LDO capable of handling up to 1 A of load current. This device features an integrated current limit, thermal shutdown, band-gap reference, and undervoltage lockout (UVLO) circuit blocks.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Internal Current Limit

The TLV1117LV internal current limit helps protect the regulator during fault conditions. During current limit, the output sources a fixed amount of current that is largely independent of the output voltage. In such a case, the output voltage is not regulated, and can be calculated by the formula: $V_{OUT} = I_{LIMIT} \times R_{LOAD}$. The PMOS pass transistor dissipates $(V_{IN} – V_{OUT}) \times I_{LIMIT}$ until thermal shutdown is triggered and the device turns off. When the device cools down, the internal thermal shutdown circuit turns the device back on. If the fault condition continues, the device cycles between current limit and thermal shutdown. See the *Thermal Protection* section for more details.

The PMOS pass transistor in the TLV1117LV has a built-in body diode that conducts current when the voltage at OUT exceeds the voltage at IN. This current is not limited; if extended reverse voltage operation is anticipated, external limiting to 5% of the rated output current is recommended.

7.3.2 Dropout Voltage

The TLV1117LV uses a PMOS pass transistor to achieve low dropout. When $(V_{IN} – V_{OUT})$ is less than the dropout voltage (V_{DO}), the PMOS pass transistor is in the linear region of operation and the input-to-output resistance is the $R_{DS(ON)}$ of the PMOS pass transistor. V_{DO} scales approximately with output current because the PMOS transistor behaves like a resistor in dropout.

As with any linear regulator, PSRR and transient response are degraded when $(V_{IN} – V_{OUT})$ approaches dropout.

7.3.3 Undervoltage Lockout

The TLV1117LV uses an undervoltage lockout (UVLO) circuit to keep the output shut off until internal circuitry is operating properly.

7.4 Device Functional Modes

7.4.1 Normal Operation

The device regulates to the nominal output voltage under the following conditions:

- The input voltage is greater than the nominal output voltage added to the dropout voltage
- The output current is less than the current limit
- The device die temperature is lower than the thermal shutdown temperature

7.4.2 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode. In this condition, the output voltage is the same the input voltage minus the dropout voltage. The transient performance of the device is significantly degraded because the pass transistor is in a triode state and no longer controls the current through the LDO. Line or load transients in dropout can result in large output voltage deviations.

Table 7-1 shows the conditions that lead to the different modes of operation.

Table 7-1. Device Functional Mode Comparison

OPERATING MODE	PARAMETER	
	V_{IN}	I_{OUT}
Normal mode	$V_{IN} > V_{OUT\ (nom)} + V_{DO}$	$I_{OUT} < I_{CL}$
Dropout mode	$V_{IN} < V_{OUT\ (nom)} + V_{DO}$	$I_{OUT} < I_{CL}$

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TLV1117LV is a low quiescent current linear regulator designed for high current applications. Unlike typical high current linear regulators, the TLV1117LV consumes significantly less quiescent current. This device delivers excellent line and load transient performance. The device is low noise, and exhibits a very good PSRR. As a result, this device is designed for high current applications that require very sensitive power-supply rails.

This regulators offer both current limit and thermal protection. The operating junction temperature range of the device is –40°C to +125°C.

8.2 Typical Application

Figure 8-1 shows a typical application circuit.

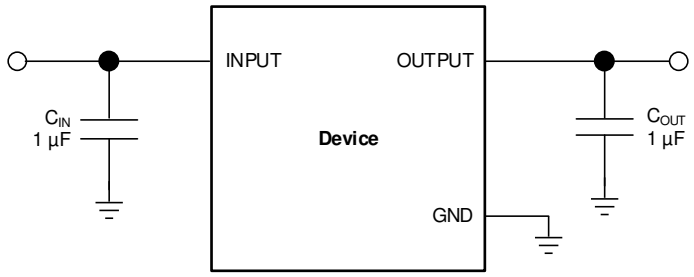


Figure 8-1. Typical Application Circuit

8.2.1 Design Requirements

For this design example, use the parameters listed in Table 8-1 as the input parameters.

Table 8-1. Design Parameters

PARAMETER	DESIGN REQUIREMENT
Input voltage	2.5 V to 3.3 V
Output voltage	1.8 V
Output current	500 mA

8.2.2 Detailed Design Procedure

8.2.2.1 Input and Output Capacitor Requirements

For stability, 1.0-µF ceramic capacitors are required at the output. Higher-valued capacitors improve transient performance. Use X5R- and X7R-type ceramic capacitors because these capacitors have minimal variation in value and equivalent series resistance (ESR) over temperature. Unlike traditional linear regulators that need a minimum ESR for stability, the TLV1117LV is specified to be stable with no ESR. Therefore, cost-effective ceramic capacitors can be used with this device. Effective output capacitance that takes bias, temperature, and aging effects into consideration must be greater than 0.5 µF to ensure stability of the device.

Although an input capacitor is not required for stability, good analog design practice is to connect a 0.1-µF to 1.0-µF, low-ESR capacitor across the IN pin and GND pin of the regulator. This capacitor counteracts reactive input sources and improves transient response, noise rejection, and ripple rejection. A higher-value capacitor can be necessary if large, fast rise-time load transients are anticipated, or if the device is not located physically

close to the power source. If source impedance is greater than 2 Ω, a 0.1-µF input capacitor can also be necessary to ensure stability.

8.2.2.2 Transient Response

As with any regulator, increasing the size of the output capacitor reduces overshoot and undershoot magnitude.

8.2.3 Application Curves

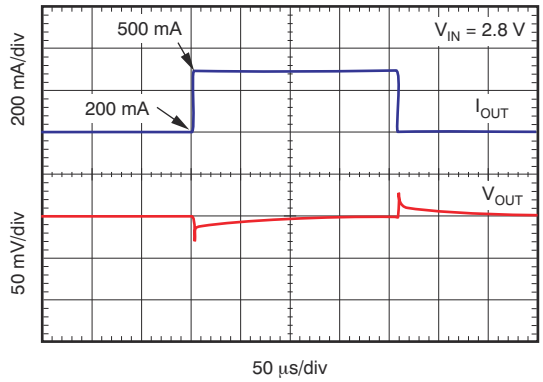


Figure 8-2. Load Transient Response 200 mA to 500 mA, C_{OUT} = 1 µF

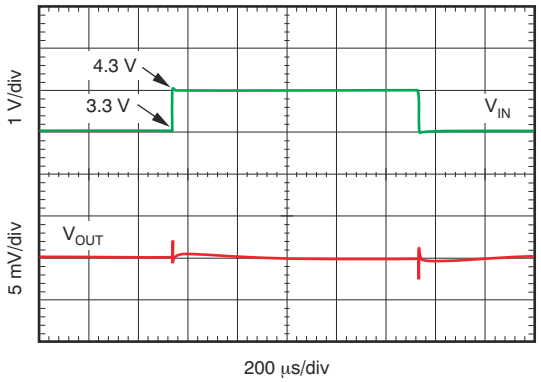


Figure 8-3. Line Transient Response V_{OUT} = 1.8 V, I_{OUT} = 500 mA

8.3 Best Design Practices

Place input and output capacitors as close to the device as possible.

Use a ceramic output capacitor.

Do not use an electrolytic output capacitor.

Do not exceed the device absolute maximum ratings.

8.4 Power Supply Recommendations

Connect a low output impedance power supply directly to the INPUT pin of the TLV1117LV. Inductive impedances between the input supply and the INPUT pin can create significant voltage excursions at the INPUT pin during start-up or load transient events.

8.5 Layout

8.5.1 Layout Guidelines

Place input and output capacitors as close to the device pins as possible. To improve characteristic AC performance (such as PSRR, output noise, and transient response), design the board with separate ground planes for V_{IN} and V_{OUT}, with the ground plane connected only at the GND pin of the device. In addition, the ground connection for the output capacitor must be connected directly to the GND pin of the device. Higher value ESR capacitors can degrade PSRR performance.

8.5.1.1 Thermal Protection

Thermal protection disables the output when the junction temperature rises to approximately 165°C, allowing the device to cool. When the junction temperature cools to approximately 145°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit can cycle on and off. This cycling limits the dissipation of the regulator, protecting the regulator from damage as a result of overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heat sink. For reliable operation, limit junction temperature to 125°C maximum. To estimate the margin of safety in a complete design (including heat sink), increase the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions.

The internal protection circuitry of the TLV1117LV is designed to protect against overload conditions. This circuitry is not intended to replace proper heat sinking. Continuously running the TLV1117LV into thermal shutdown degrades device reliability.

8.5.1.2 Power Dissipation

The ability to remove heat from the die is different for each package type, presenting different considerations in the printed circuit board (PCB) layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air. Performance data for JEDEC low and high-K boards are given in the *Thermal Information* table. Using heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers also improves heat-sink effectiveness.

Power dissipation depends on input voltage and load conditions. Power dissipation (P_D) is equal to the product of the output current and the voltage drop across the output pass element, as shown in Equation 1:

$$P_D = (V_{IN} - V_{OUT})\, I_{OUT} \quad (1)$$

8.5.2 Layout Example

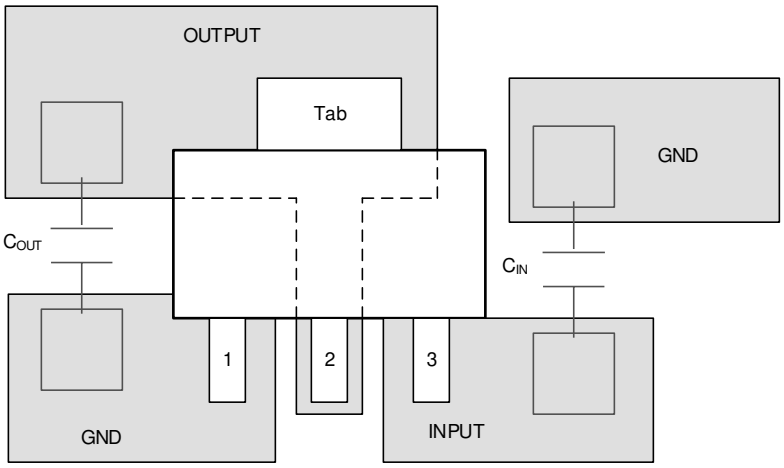


Figure 8-4. Layout Example

9 Device and Documentation Support

9.1 Device Support

9.1.1 Development Support

9.1.1.1 Evaluation Module

An evaluation module (EVM) is available to assist in the initial circuit performance evaluation using the TLV1117LV. The TLV1117LV33EVM-714 evaluation module (and related user's guide) can be requested at the TI website through the product folders or purchased directly from the TI eStore.

9.1.1.2 Spice Models

Computer simulation of circuit performance using SPICE is often useful when analyzing the performance of analog circuits and systems. A SPICE model for the TLV1117LV is available through the product folders under *Tools & Software*.

9.1.2 Device Nomenclature

Table 9-1. Available Options(1)

PRODUCT	V_{OUT}
TLV1117LV**xxyyyz**	**xx** is the nominal output voltage (for example 33 = 3.3 V). **yyy** is the package designator. **z** is the package quantity.

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

9.2 Documentation Support

9.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *TLV1117LVxxEVM-714 Evaluation Module* user's guide

9.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.4 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.5 Trademarks

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9.6 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.7 Glossary

TI Glossary — This glossary lists and explains terms, acronyms, and definitions.

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV1117LV12DCYR	ACTIVE	SOT-223	DCY	4	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	SI	Samples
TLV1117LV12DCYT	OBSOLETE	SOT-223	DCY	4		TBD	Call TI	Call TI	-40 to 125	SI	
TLV1117LV15DCYR	ACTIVE	SOT-223	DCY	4	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	VR	Samples
TLV1117LV15DCYT	OBSOLETE	SOT-223	DCY	4		TBD	Call TI	Call TI	-40 to 125	VR	
TLV1117LV18DCYR	ACTIVE	SOT-223	DCY	4	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	SH	Samples
TLV1117LV18DCYT	ACTIVE	SOT-223	DCY	4	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	SH	Samples
TLV1117LV25DCYR	ACTIVE	SOT-223	DCY	4	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	VS	Samples
TLV1117LV25DCYT	ACTIVE	SOT-223	DCY	4	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	VS	Samples
TLV1117LV28DCYR	ACTIVE	SOT-223	DCY	4	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	VT	Samples
TLV1117LV28DCYT	OBSOLETE	SOT-223	DCY	4		TBD	Call TI	Call TI	-40 to 125	VT	
TLV1117LV30DCYR	ACTIVE	SOT-223	DCY	4	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	VU	Samples
TLV1117LV30DCYT	OBSOLETE	SOT-223	DCY	4		TBD	Call TI	Call TI	-40 to 125	VU	
TLV1117LV33DCYR	ACTIVE	SOT-223	DCY	4	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	TJ	Samples
TLV1117LV33DCYT	OBSOLETE	SOT-223	DCY	4		TBD	Call TI	Call TI	-40 to 125	TJ	

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

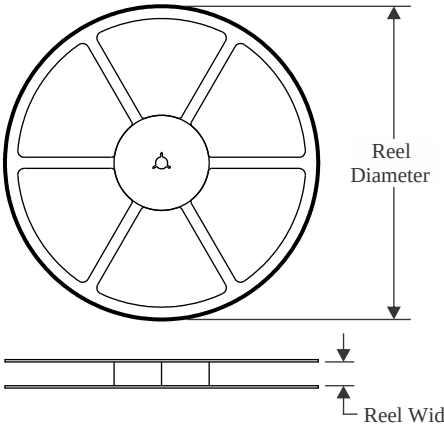
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

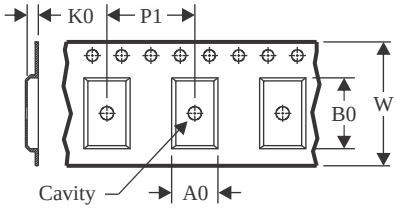
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

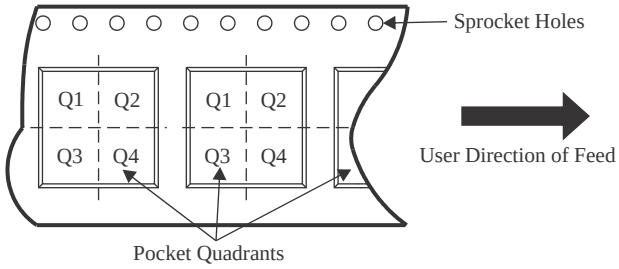


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

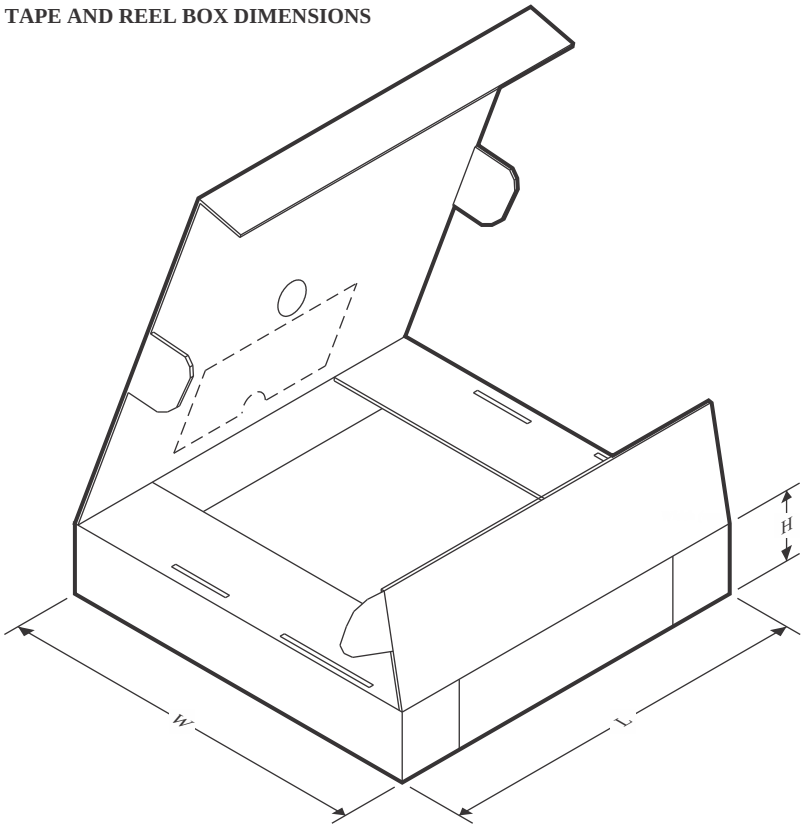
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV1117LV12DCYR	SOT-223	DCY	4	2500	330.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3
TLV1117LV15DCYR	SOT-223	DCY	4	2500	330.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3
TLV1117LV18DCYR	SOT-223	DCY	4	2500	330.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3
TLV1117LV18DCYT	SOT-223	DCY	4	250	180.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3
TLV1117LV25DCYR	SOT-223	DCY	4	2500	330.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3
TLV1117LV25DCYT	SOT-223	DCY	4	250	180.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3
TLV1117LV28DCYR	SOT-223	DCY	4	2500	330.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3
TLV1117LV30DCYR	SOT-223	DCY	4	2500	330.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3
TLV1117LV33DCYR	SOT-223	DCY	4	2500	330.0	12.4	7.05	7.4	1.9	8.0	12.0	Q3

TAPE AND REEL BOX DIMENSIONS

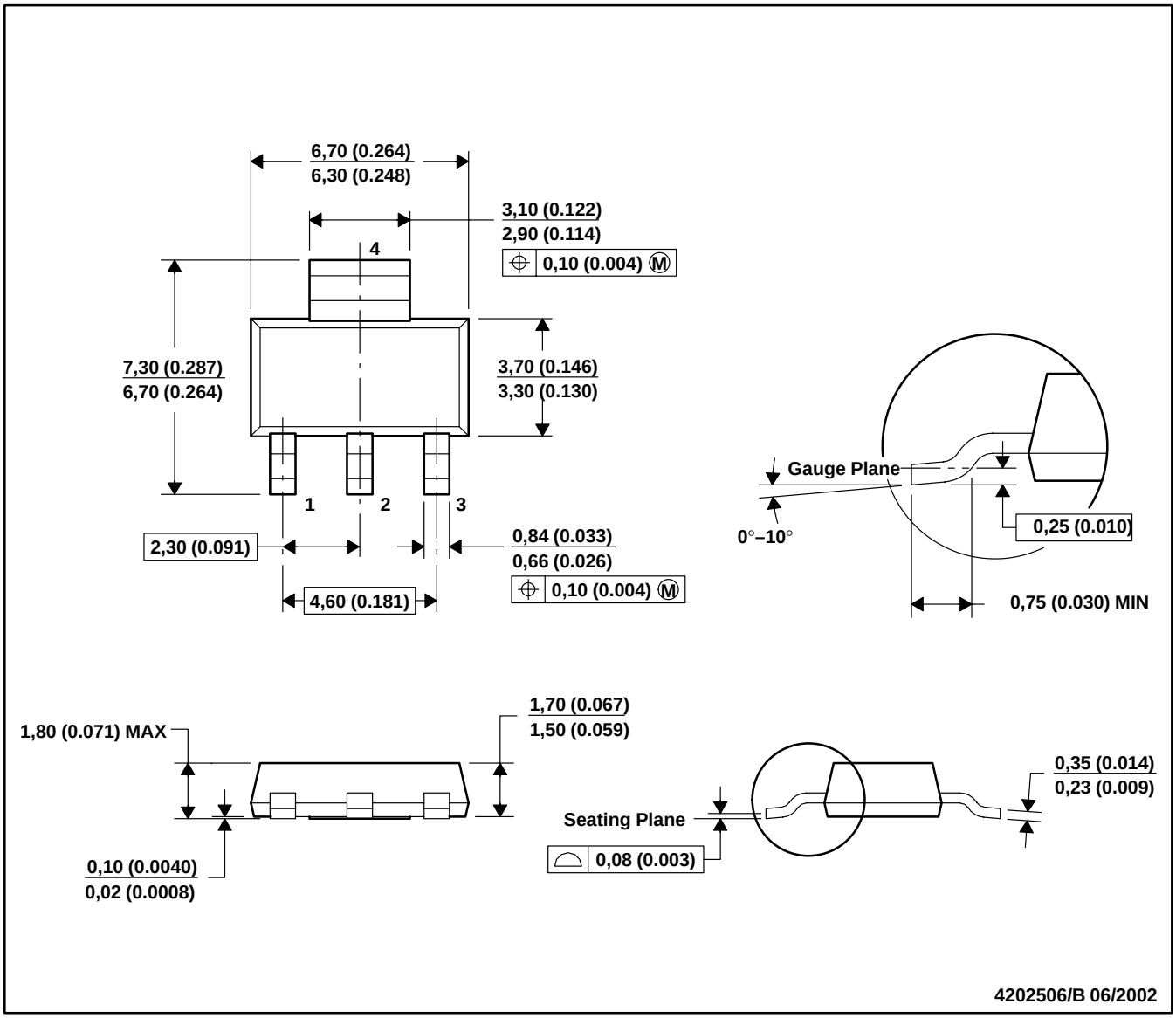


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV1117LV12DCYR	SOT-223	DCY	4	2500	340.0	340.0	38.0
TLV1117LV15DCYR	SOT-223	DCY	4	2500	340.0	340.0	38.0
TLV1117LV18DCYR	SOT-223	DCY	4	2500	340.0	340.0	38.0
TLV1117LV18DCYT	SOT-223	DCY	4	250	340.0	340.0	38.0
TLV1117LV25DCYR	SOT-223	DCY	4	2500	340.0	340.0	38.0
TLV1117LV25DCYT	SOT-223	DCY	4	250	340.0	340.0	38.0
TLV1117LV28DCYR	SOT-223	DCY	4	2500	340.0	340.0	38.0
TLV1117LV30DCYR	SOT-223	DCY	4	2500	340.0	340.0	38.0
TLV1117LV33DCYR	SOT-223	DCY	4	2500	340.0	340.0	38.0

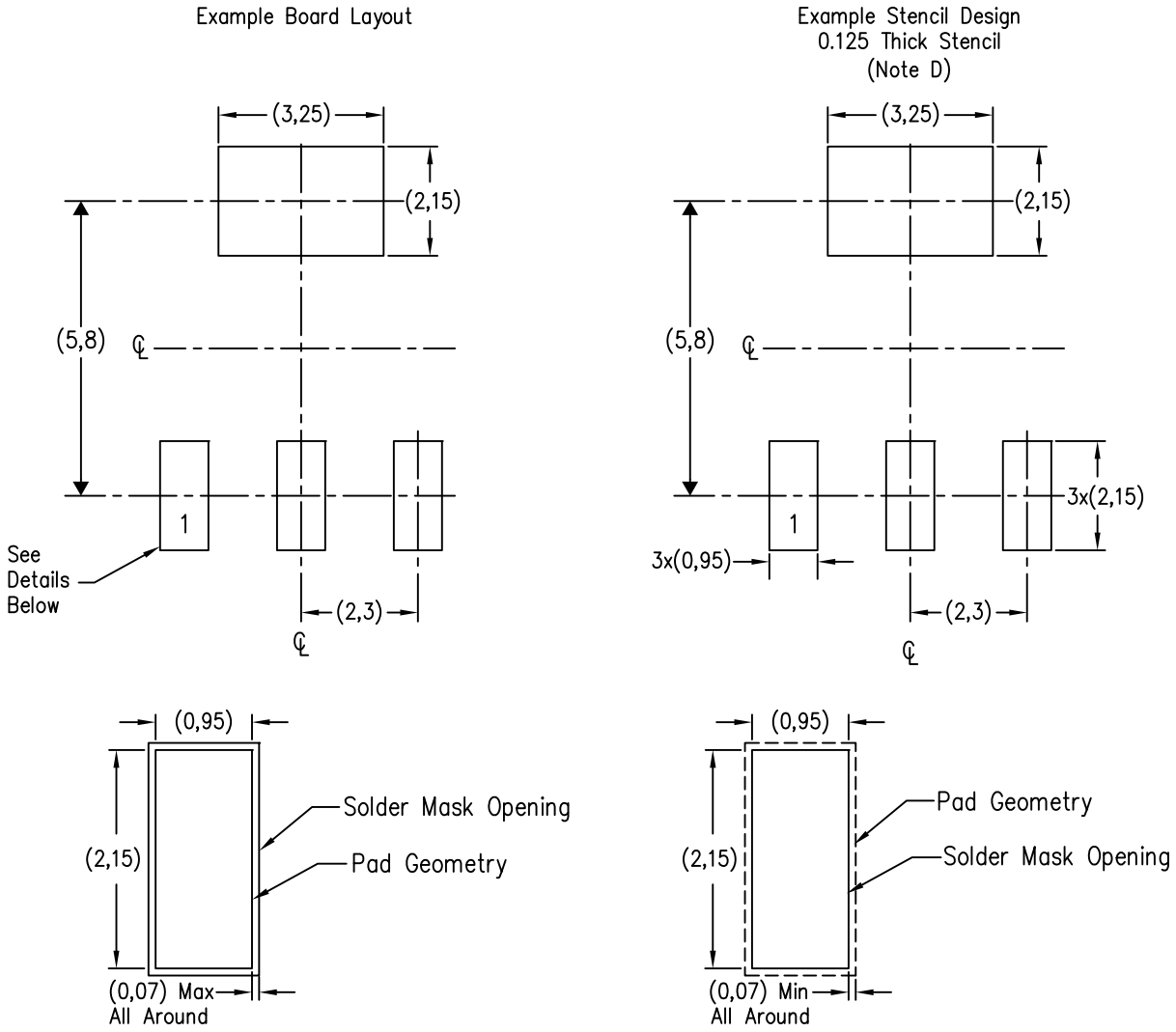
MPDS094A – APRIL 2001 – REVISED JUNE 2002

DCY (R-PDSO-G4) **PLASTIC SMALL-OUTLINE**



NOTES: A. All linear dimensions are in millimeters (inches).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion.
D. Falls within JEDEC TO-261 Variation AA.

DCY (R–PDSO–G4) PLASTIC SMALL OUTLINE



NOTES:

A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil recommendations. Refer to IPC 7525 for stencil design considerations.

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